

PATENT APPLICATION

Sheet 1 of 6

FORM PTO-1449		ATTY. DOCKET NO. 200316547-1	APPLICATION NO. 10/799961	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT Randy L. Hoffman, et al.		
(Use several sheets if necessary)		FILING DATE <i>Received 3/12/04</i>	GROUP <i>2815</i>	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
WFK	1A 5,744,864	08/28/1998	Cillessen, et al.	
WFK	1B 2003/0047785	03/13/2003	Kawasaki, et al.	
WFK	1C 2003/0111663	06/19/2003	Yagi	
WFK	1D 2003/0218221	11/27/2003	Wager, III, et al.	
WFK	1E 2003/0218222	11/27/2003	Wager, III, et al.	
WFK	1F 60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
WFK	1G 10/763,353	01/23/2004		Semiconductor Device
WFK	1H 10/763,354	01/23/2004		Transistor Including a Deposited Channel Region Having A ...
	1I			
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
WFK	1L	WO 97/06544	02/20/1997	Cillessen, et al.		E
WFK	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
WFK	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
WFK	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

EXAMINER

William F. Craig

DATE CONSIDERED

1/16/06

PATENT APPLICATION

Sheet 2 of 6

FORM PTO-1449		ATTY. DOCKET NO. 200316547-1	APPLICATION NO. 10179961	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT Randy L. Hoffman, et al.		
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EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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2L					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transition Metal Oxides", SPIE Vol. 2697, pp. 520-527.
WFK	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microelectronic Engineering, Vol. 35, pp. 71-74 (1997).
WFK	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO ₂ Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

EXAMINER	DATE CONSIDERED
William F. Kraig	116106

PATENT APPLICATION

Sheet 3 of 6

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT		
(Use several sheets if necessary)		Randy L. Hoffman, et al.		
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		Herewith 3/12/04	2815	

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
WFK	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
WFK	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

EXAMINER	DATE CONSIDERED
<i>William F. Kraig</i>	116106

PATENT APPLICATION

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FORM PTO-1449		ATTY. DOCKET NO. 200316547-1	APPLICATION NO. 10/79961	CONFIRMATION NO.
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4M					
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4P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
WFK	4R	Pallecchi, Ilaria, et al. "SrTiO ₃ -based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
WFK	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

EXAMINER 	DATE CONSIDERED 116/06
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PATENT APPLICATION

Sheet 5 of 6

FORM PTO-1449		ATTY. DOCKET NO. 200316547-1	APPLICATION NO. 10/799961	CONFIRMATION NO.
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(Use several sheets if necessary)		FILING DATE Hermann 3/12/04	GROUP 2815	

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
WFK	5R	Uneno, K., et al. "Field-effect transistor on SrTiO ₃ with sputtered Al ₂ O ₃ gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
WFK	5S	Wöllensteien, Jürgen, et al., "An insulated gate thin-film transistor using SnO ₂ as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

EXAMINER <i>William F. Krey</i>	DATE CONSIDERED 116106
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PATENT APPLICATION

Sheet 6 of 6

FORM PTO-1449		ATTY. DOCKET NO. 200316547-1	APPLICATION NO. 10/799961	CONFIRMATION NO.
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6O					
6P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

WFK	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO ₃ Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
WFK	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
WFK	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLEAD_" Research Disclosure, p. 890 (July 1998).

EXAMINER	DATE CONSIDERED
<i>William F. Kray</i>	11/6/06



PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 2

Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Application Number	10/799961
		Filing Date	Mar 12, 2004
		First Named Inventor	Randy Hoffman
		Art Unit	2815
		Examiner Name	William F. Kraig
		Attorney Docket Number	200316547-1

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ² -Number ⁴ -Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
WFK	WO 02/09157		01-31-2002	Motorola	

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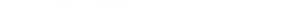
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Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Application Number	10/799961
		Filing Date	Mar 12, 2004
		First Named Inventor	Randy Hoffman
		Art Unit	2815
		Examiner Name	William F. Koenig
Sheet	2	of	2
		Attorney Docket Number	200316547-1

NON-PATENT LITERATURE DOCUMENTS

Examiner Signature		Date Considered	11/6/06
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